

Process: Bip 1 2 - 5

Complementary 40V 高速 Bipolar

Key Features

Absolute Maximum Rating: 40V

NPN (Emitter 2.0um x 4.0um):

hFE 100 @Ic=100uA, Vce=5V

Va 350V

BVceo min.40V

ft 2.9GHz @Vce=20V

fmax 3.9GHz @Vce=20V

Vertical PNP (Emitter 2.0um x 4.0um):

hFE 80 @Ic=-100uA, Vce=-5V

Va 50V

BVceo min. -40V

ft 3.7GHz @Vce=-20V

fmax 2.9GHz @Vce=-20V

Lateral PNP (Emitter 10umx 10um, Base 12um):

hFE 150 @Ic=-10uA, Vce=-5V

Va 90V

BVceo min.40V

ft 数十MHz (推測値)

Pch JFET (Gate W,L= 20um,10um)

Vp typ.1.0V @Vd=5V, 1uA

Idss typ. 25uA @Vd=5V

BVceo min. 40V @100uA

Resistor:

HR POLY · Poly(200 ohm/sq.) · Base(3500 ohm/sq)

Capacitor:

PIM(0.46fF/um²)

Metal:

2layers